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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	4075
Number of Logic Elements/Cells	52160
Total RAM Bits	2764800
Number of I/O	250
Number of Gates	-
Voltage - Supply	0.92V ~ 0.98V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/xilinx/xc7s50-l1fgga484i">https://www.e-xfl.com/product-detail/xilinx/xc7s50-l1fgga484i</a>

Table 2: Recommended Operating Conditions<sup>(1)(2)</sup>

Symbol	Description	Min	Typ	Max	Units
<b>FPGA Logic</b>					
V <sub>CCINT</sub> <sup>(3)</sup>	For -2 and -1 (1.0V) devices: internal supply voltage.	0.95	1.00	1.05	V
	For -1L (0.95V) devices: internal supply voltage.	0.92	0.95	0.98	V
V <sub>CCAUX</sub>	Auxiliary supply voltage.	1.71	1.80	1.89	V
V <sub>CCBRAM</sub> <sup>(3)</sup>	For -2 and -1 (1.0V) devices: block RAM supply voltage.	0.95	1.00	1.05	V
	For -1L (0.95V) devices: block RAM supply voltage.	0.92	0.95	0.98	V
V <sub>CCO</sub> <sup>(4)(5)</sup>	Supply voltage for HR I/O banks.	1.14	—	3.465	V
V <sub>IN</sub> <sup>(6)</sup>	I/O input voltage.	-0.20	—	V <sub>CCO</sub> + 0.20	V
	I/O input voltage (when V <sub>CCO</sub> = 3.3V) for V <sub>REF</sub> and differential I/O standards except TMDS_33. <sup>(7)</sup>	-0.20	—	2.625	V
I <sub>IN</sub> <sup>(8)</sup>	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	—	—	10	mA
V <sub>CCBATT</sub> <sup>(9)</sup>	Battery voltage.	1.0	—	1.89	V
<b>XADC</b>					
V <sub>CCADC</sub>	XADC supply relative to GNDADC.	1.71	1.80	1.89	V
V <sub>REFP</sub>	Externally supplied reference voltage.	1.20	1.25	1.30	V
<b>Temperature</b>					
T <sub>J</sub>	Junction temperature operating range for commercial (C) temperature devices.	0	—	85	°C
	Junction temperature operating range for industrial (I) temperature devices.	-40	—	100	°C
	Junction temperature operating range for expanded (Q) temperature devices.	-40	—	125	°C

**Notes:**

- All voltages are relative to ground.
- For the design of the power distribution system consult the *7 Series FPGAs PCB Design Guide* (UG483) [Ref 5].
- If V<sub>CCINT</sub> and V<sub>CCBRAM</sub> are operating at the same voltage, V<sub>CCINT</sub> and V<sub>CCBRAM</sub> should be connected to the same supply.
- Configuration data is retained even if V<sub>CCO</sub> drops to 0V.
- Includes V<sub>CCO</sub> of 1.2V, 1.35V, 1.5V, 1.8V, 2.5V, and 3.3V at ±5%.
- The lower absolute voltage specification always applies.
- See Table 9 for TMDS\_33 specifications.
- A total of 200 mA per bank should not be exceeded.
- V<sub>CCBATT</sub> is required only when using bitstream encryption. If battery is not used, connect V<sub>CCBATT</sub> to either ground or V<sub>CCAUX</sub>.

Table 4:  $V_{IN}$  Maximum Allowed AC Voltage Overshoot and Undershoot for HR I/O Banks<sup>(1)(2)</sup>

AC Voltage Overshoot	% of UI at -40°C to 125°C	AC Voltage Undershoot	% of UI at -40°C to 125°C
$V_{CCO} + 0.55$	100	-0.40	100
		-0.45	61.7
		-0.50	25.8
		-0.55	11.0
$V_{CCO} + 0.60$	46.6	-0.60	4.77
$V_{CCO} + 0.65$	21.2	-0.65	2.10
$V_{CCO} + 0.70$	9.75	-0.70	0.94
$V_{CCO} + 0.75$	4.55	-0.75	0.43
$V_{CCO} + 0.80$	2.15	-0.80	0.20
$V_{CCO} + 0.85$	1.02	-0.85	0.09
$V_{CCO} + 0.90$	0.49	-0.90	0.04
$V_{CCO} + 0.95$	0.24	-0.95	0.02

**Notes:**

1. A total of 200 mA per bank should not be exceeded.
2. The peak voltage of the overshoot or undershoot, and the duration above  $V_{CCO} + 0.20V$  or below GND – 0.20V, must not exceed the values in this table.

Table 5: Typical Quiescent Supply Current<sup>(1)(2)(3)</sup>

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
$I_{CCINTQ}$	Quiescent $V_{CCINT}$ supply current.	XC7S6	36	36	36	36	36	32	mA
		XC7S15	36	36	36	36	36	32	mA
		XC7S25	48	48	48	48	48	43	mA
		XC7S50	95	95	95	95	95	59	mA
		XC7S75	148	148	148	148	148	134	mA
		XC7S100	148	148	148	148	148	134	mA
		XA7S6	N/A	36	N/A	36	36	N/A	mA
		XA7S15	N/A	36	N/A	36	36	N/A	mA
		XA7S25	N/A	48	N/A	48	48	N/A	mA
		XA7S50	N/A	95	N/A	95	95	N/A	mA
		XA7S75	N/A	148	N/A	148	148	N/A	mA
		XA7S100	N/A	148	N/A	148	148	N/A	mA

Table 5: Typical Quiescent Supply Current<sup>(1)(2)(3)</sup> (Cont'd)

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
$I_{CCBRAMQ}$	Quiescent $V_{CCBRAM}$ supply current.	XC7S6	1	1	1	1	1	1	mA
		XC7S15	1	1	1	1	1	1	mA
		XC7S25	1	1	1	1	1	1	mA
		XC7S50	2	2	2	2	2	1	mA
		XC7S75	9	9	9	9	9	8	mA
		XC7S100	9	9	9	9	9	8	mA
		XA7S6	N/A	1	N/A	1	1	N/A	mA
		XA7S15	N/A	1	N/A	1	1	N/A	mA
		XA7S25	N/A	1	N/A	1	1	N/A	mA
		XA7S50	N/A	2	N/A	2	2	N/A	mA
		XA7S75	N/A	9	N/A	9	9	N/A	mA
		XA7S100	N/A	9	N/A	9	9	N/A	mA

**Notes:**

1. Typical values are specified at nominal voltage, 85°C junction temperature ( $T_j$ ) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator spreadsheet tool [Ref 6] to estimate static power consumption for conditions other than those specified.

## Power-On/Off Power Supply Sequencing

The recommended power-on sequence is  $V_{CCINT}$ ,  $V_{CCBRAM}$ ,  $V_{CCAUX}$ , and  $V_{CCO}$  to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If  $V_{CCINT}$  and  $V_{CCBRAM}$  have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If  $V_{CCAUX}$  and  $V_{CCO}$  have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For  $V_{CCO}$  voltages of 3.3V in HR I/O banks and configuration bank 0 the following conditions apply.

- The voltage difference between  $V_{CCO}$  and  $V_{CCAUX}$  must not exceed 2.625V for longer than  $T_{VCCO2VCCAUX}$  for each power-on/off cycle to maintain device reliability levels.
- The  $T_{VCCO2VCCAUX}$  time can be allocated in any percentage between the power-on and power-off ramps.

There is no recommended sequence for supplies not discussed in this section.

## LVDS DC Specifications (LVDS\_25)

Table 11: LVDS\_25 DC Specifications<sup>(1)</sup>

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
$V_{CCO}$	Supply voltage.		2.375	2.500	2.625	V
$V_{OH}$	Output High voltage for Q and $\bar{Q}$ .	$R_T = 100\Omega$ across Q and $\bar{Q}$ signals.	–	–	1.675	V
$V_{OL}$	Output Low voltage for Q and $\bar{Q}$ .	$R_T = 100\Omega$ across Q and $\bar{Q}$ signals.	0.700	–	–	V
$V_{ODIFF}$	Differential output voltage: $(Q - \bar{Q})$ , Q = High $(\bar{Q} - Q)$ , $\bar{Q}$ = High	$R_T = 100\Omega$ across Q and $\bar{Q}$ signals.	247	350	600	mV
$V_{OCM}$	Output common-mode voltage.	$R_T = 100\Omega$ across Q and $\bar{Q}$ signals.	1.000	1.250	1.425	V
$V_{IDIFF}$	Differential input voltage: $(Q - \bar{Q})$ , Q = High $(\bar{Q} - Q)$ , $\bar{Q}$ = High		100	350	600	mV
$V_{ICM}$	Input common-mode voltage.		0.300	1.200	1.500	V

**Notes:**

1. Differential inputs for LVDS\_25 can be placed in banks with  $V_{CCO}$  levels that are different from the required level for outputs. Consult the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3] for more information.

# AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications from the Vivado® Design Suite as outlined in [Table 12](#).

**Table 12: Speed Specification Version By Device**

2018.2.1	Device
1.23	XC7S6, XC7S15, XC7S25, XC7S50, XC7S75, XC7S100
1.16	XA7S6, XA7S15, XA7S25, XA7S50, XA7S75, XA7S100

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows.

## Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

## Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

## Production Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

# Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Spartan-7 FPGAs.

## Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. [Table 13](#) correlates the current status of each Spartan-7 device on a per speed grade basis.

**Table 13: Spartan-7 Device Speed Grade Designations**

Device	Speed Grade, Temperature Range, and $V_{CCINT}$ Operating Voltage		
	Advance	Preliminary	Production
XC7S6			-2C (1.0V), -2I (1.0V), -1C (1.0V), -1I (1.0V), -1Q (1.0V), and -1LI (0.95V) <sup>(1)</sup>
XC7S15			-2C (1.0V), -2I (1.0V), -1C (1.0V), -1I (1.0V), -1Q (1.0V), and -1LI (0.95V) <sup>(1)</sup>
XC7S25			-2C (1.0V), -2I (1.0V), -1C (1.0V), -1I (1.0V), -1Q (1.0V), and -1LI (0.95V) <sup>(1)</sup>
XC7S50			-2C (1.0V), -2I (1.0V), -1C (1.0V), -1I (1.0V), -1Q (1.0V), and -1LI (0.95V) <sup>(1)</sup>
XC7S75			-2C (1.0V), -2I (1.0V), -1C (1.0V), -1I (1.0V), -1Q (1.0V), and -1LI (0.95V) <sup>(1)</sup>
XC7S100			-2C (1.0V), -2I (1.0V), -1C (1.0V), -1I (1.0V), -1Q (1.0V), and -1LI (0.95V) <sup>(1)</sup>
XA7S6			-2I (1.0V), -1I (1.0V), -1Q (1.0V)
XA7S15			-2I (1.0V), -1I (1.0V), -1Q (1.0V)
XA7S25			-2I (1.0V), -1I (1.0V), -1Q (1.0V)
XA7S50			-2I (1.0V), -1I (1.0V), -1Q (1.0V)
XA7S75			-2I (1.0V), -1I (1.0V), -1Q (1.0V)
XA7S100			-2I (1.0V), -1I (1.0V), -1Q (1.0V)

**Notes:**

1. The lowest power -1LI devices, where  $V_{CCINT} = 0.95V$ , are listed in the Vivado Design Suite as -1IL.

## Production Silicon and Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

[Table 14](#) lists the production released Spartan-7 device, speed grade, and the minimum corresponding supported speed specification version and software revisions. The software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 17: IOB High Range (HR) Switching Characteristics

I/O Standard	T <sub>IOP1</sub>			T <sub>IOPP</sub>			T <sub>IOTP</sub>			Units	
	V <sub>CCINT</sub> Operating Voltage and Speed Grade										
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V		
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L		
LVTTL_S4	1.34	1.41	1.41	3.93	4.18	4.18	3.96	4.20	4.20	ns	
LVTTL_S8	1.34	1.41	1.41	3.66	3.92	3.92	3.69	3.93	3.93	ns	
LVTTL_S12	1.34	1.41	1.41	3.65	3.90	3.90	3.68	3.91	3.91	ns	
LVTTL_S16	1.34	1.41	1.41	3.19	3.45	3.45	3.22	3.46	3.46	ns	
LVTTL_S24	1.34	1.41	1.41	3.41	3.67	3.67	3.44	3.68	3.68	ns	
LVTTL_F4	1.34	1.41	1.41	3.38	3.64	3.64	3.41	3.65	3.65	ns	
LVTTL_F8	1.34	1.41	1.41	2.87	3.12	3.12	2.90	3.13	3.13	ns	
LVTTL_F12	1.34	1.41	1.41	2.85	3.10	3.10	2.88	3.12	3.12	ns	
LVTTL_F16	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns	
LVTTL_F24	1.34	1.41	1.41	2.65	2.90	2.90	2.68	2.91	2.91	ns	
LVDS_25	0.81	0.88	0.88	1.41	1.67	1.67	1.44	1.68	1.68	ns	
MINI_LVDS_25	0.81	0.88	0.88	1.40	1.65	1.65	1.43	1.66	1.66	ns	
BLVDS_25	0.81	0.88	0.88	1.96	2.21	2.21	1.99	2.23	2.23	ns	
RSDS_25 (point to point)	0.81	0.88	0.88	1.40	1.65	1.65	1.43	1.66	1.66	ns	
PPDS_25	0.81	0.88	0.88	1.41	1.67	1.67	1.44	1.68	1.68	ns	
TMDS_33	0.81	0.88	0.88	1.54	1.79	1.79	1.57	1.80	1.80	ns	
PCI33_3	1.32	1.39	1.39	3.22	3.48	3.48	3.25	3.49	3.49	ns	
HSUL_12_S	0.75	0.82	0.82	1.93	2.18	2.18	1.96	2.20	2.20	ns	
HSUL_12_F	0.75	0.82	0.82	1.41	1.67	1.67	1.44	1.68	1.68	ns	
DIFF_HSUL_12_S	0.76	0.83	0.83	1.93	2.18	2.18	1.96	2.20	2.20	ns	
DIFF_HSUL_12_F	0.76	0.83	0.83	1.41	1.67	1.67	1.44	1.68	1.68	ns	
MOBILE_DDR_S	0.84	0.91	0.91	1.80	2.06	2.06	1.83	2.07	2.07	ns	
MOBILE_DDR_F	0.84	0.91	0.91	1.51	1.76	1.76	1.54	1.77	1.77	ns	
DIFF_MOBILE_DDR_S	0.78	0.85	0.85	1.82	2.07	2.07	1.85	2.09	2.09	ns	
DIFF_MOBILE_DDR_F	0.78	0.85	0.85	1.57	1.82	1.82	1.60	1.84	1.84	ns	
HSTL_I_S	0.75	0.82	0.82	1.74	1.99	1.99	1.77	2.01	2.01	ns	
HSTL_II_S	0.73	0.80	0.80	1.54	1.79	1.79	1.57	1.80	1.80	ns	
HSTL_I_18_S	0.75	0.82	0.82	1.41	1.67	1.67	1.44	1.68	1.68	ns	
HSTL_II_18_S	0.75	0.81	0.81	1.54	1.79	1.79	1.57	1.80	1.80	ns	
DIFF_HSTL_I_S	0.76	0.83	0.83	1.71	1.96	1.96	1.74	1.98	1.98	ns	
DIFF_HSTL_II_S	0.76	0.83	0.83	1.63	1.88	1.88	1.66	1.90	1.90	ns	
DIFF_HSTL_I_18_S	0.79	0.86	0.86	1.51	1.76	1.76	1.54	1.77	1.77	ns	
DIFF_HSTL_II_18_S	0.78	0.85	0.85	1.58	1.84	1.84	1.61	1.85	1.85	ns	
HSTL_I_F	0.75	0.82	0.82	1.22	1.48	1.48	1.25	1.49	1.49	ns	
HSTL_II_F	0.73	0.80	0.80	1.24	1.49	1.49	1.27	1.51	1.51	ns	
HSTL_I_18_F	0.75	0.82	0.82	1.26	1.51	1.51	1.29	1.52	1.52	ns	

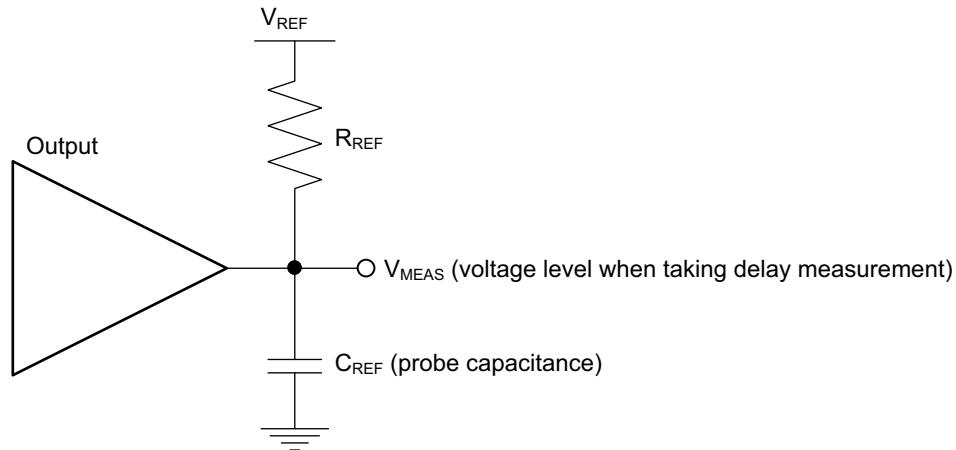
Table 17: IOB High Range (HR) Switching Characteristics (Cont'd)

I/O Standard	T <sub>IOP1</sub>			T <sub>IOOP</sub>			T <sub>IOTP</sub>			Units	
	V <sub>CCINT</sub> Operating Voltage and Speed Grade										
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V		
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L		
LVCMOS15_F8	0.86	0.93	0.93	1.72	1.98	1.98	1.75	1.99	1.99	ns	
LVCMOS15_F12	0.86	0.93	0.93	1.47	1.73	1.73	1.50	1.74	1.74	ns	
LVCMOS15_F16	0.86	0.93	0.93	1.46	1.71	1.71	1.49	1.73	1.73	ns	
LVCMOS12_S4	0.95	1.02	1.02	2.69	2.95	2.95	2.72	2.96	2.96	ns	
LVCMOS12_S8	0.95	1.02	1.02	2.21	2.46	2.46	2.24	2.48	2.48	ns	
LVCMOS12_S12	0.95	1.02	1.02	1.91	2.17	2.17	1.94	2.18	2.18	ns	
LVCMOS12_F4	0.95	1.02	1.02	2.10	2.35	2.35	2.13	2.37	2.37	ns	
LVCMOS12_F8	0.95	1.02	1.02	1.66	1.92	1.92	1.69	1.93	1.93	ns	
LVCMOS12_F12	0.95	1.02	1.02	1.51	1.76	1.76	1.54	1.77	1.77	ns	
SSTL135_S	0.75	0.82	0.82	1.47	1.73	1.73	1.50	1.74	1.74	ns	
SSTL15_S	0.68	0.75	0.75	1.43	1.68	1.68	1.46	1.69	1.69	ns	
SSTL18_I_S	0.75	0.82	0.82	1.79	2.04	2.04	1.82	2.06	2.06	ns	
SSTL18_II_S	0.75	0.82	0.82	1.43	1.68	1.68	1.46	1.70	1.70	ns	
DIFF_SSTL135_S	0.76	0.83	0.83	1.47	1.73	1.73	1.50	1.74	1.74	ns	
DIFF_SSTL15_S	0.76	0.83	0.83	1.43	1.68	1.68	1.46	1.69	1.69	ns	
DIFF_SSTL18_I_S	0.79	0.86	0.86	1.80	2.06	2.06	1.83	2.07	2.07	ns	
DIFF_SSTL18_II_S	0.79	0.86	0.86	1.51	1.76	1.76	1.54	1.77	1.77	ns	
SSTL135_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns	
SSTL15_F	0.68	0.75	0.75	1.19	1.45	1.45	1.22	1.46	1.46	ns	
SSTL18_I_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns	
SSTL18_II_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns	
DIFF_SSTL135_F	0.76	0.83	0.83	1.24	1.49	1.49	1.27	1.51	1.51	ns	
DIFF_SSTL15_F	0.76	0.83	0.83	1.19	1.45	1.45	1.22	1.46	1.46	ns	
DIFF_SSTL18_I_F	0.79	0.86	0.86	1.35	1.60	1.60	1.38	1.62	1.62	ns	
DIFF_SSTL18_II_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns	

Table 18 specifies the values of T<sub>IOTPHZ</sub> and T<sub>IOBUFDISABLE</sub>. T<sub>IOTPHZ</sub> is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). T<sub>IOBUFDISABLE</sub> is described as the IOB delay from IBUFDISABLE to O output. In HR I/O banks, the internal IN\_TERM termination turn-off time is always faster than T<sub>IOTPHZ</sub> when the INTERMDISABLE pin is used.

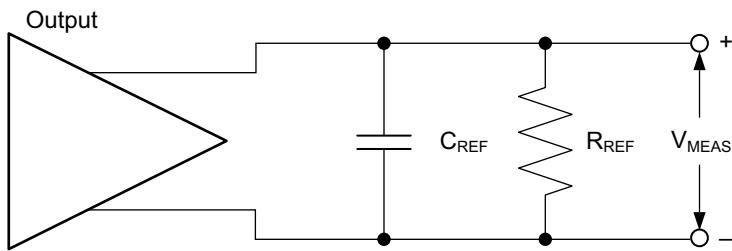
## Output Delay Measurements

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in [Figure 1](#) and [Figure 2](#).



X16654-092616

**Figure 1: Single-ended Test Setup**



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**Figure 2: Differential Test Setup**

Parameters  $V_{REF}$ ,  $R_{REF}$ ,  $C_{REF}$ , and  $V_{MEAS}$  fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from [Table 20](#).
2. Record the time to  $V_{MEAS}$ .
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to  $V_{MEAS}$ .
5. Compare the results of [step 2](#) and [step 4](#). The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Table 20: Output Delay Measurement Methodology

Description	I/O Standard Attribute	$R_{REF}$ ( $\Omega$ )	$C_{REF}$ <sup>(1)</sup> (pF)	$V_{MEAS}$ (V)	$V_{REF}$ (V)
LVC MOS, 1.2V	LVC MOS12	1M	0	0.6	0
LVC MOS, 1.5V	LVC MOS15	1M	0	0.75	0
LVC MOS, 1.8V	LVC MOS18	1M	0	0.9	0
LVC MOS, 2.5V	LVC MOS25	1M	0	1.25	0
LVC MOS, 3.3V	LVC MOS33	1M	0	1.65	0
LV TTL, 3.3V	LV TTL	1M	0	1.65	0
PCI33, 3.3V	PCI33_3	25	10	1.65	0
HSTL (high-speed transceiver logic), Class I, 1.2V	HSTL_I_12	50	0	$V_{REF}$	0.6
HSTL, Class I, 1.5V	HSTL_I	50	0	$V_{REF}$	0.75
HSTL, Class II, 1.5V	HSTL_II	25	0	$V_{REF}$	0.75
HSTL, Class I, 1.8V	HSTL_I_18	50	0	$V_{REF}$	0.9
HSTL, Class II, 1.8V	HSTL_II_18	25	0	$V_{REF}$	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	50	0	$V_{REF}$	0.6
SSTL12, 1.2V	SSTL12	50	0	$V_{REF}$	0.6
SSTL135/SSTL135_R, 1.35V	SSTL135, SSTL135_R	50	0	$V_{REF}$	0.675
SSTL15/SSTL15_R, 1.5V	SSTL15, SSTL15_R	50	0	$V_{REF}$	0.75
SSTL (stub-series terminated logic), Class I & Class II, 1.8V	SSTL18_I, SSTL18_II	50	0	$V_{REF}$	0.9
DIFF_MOBILE_DDR, 1.8V	DIFF_MOBILE_DDR	50	0	$V_{REF}$	0.9
DIFF_HSTL, Class I, 1.2V	DIFF_HSTL_I_12	50	0	$V_{REF}$	0.6
DIFF_HSTL, Class I & II, 1.5V	DIFF_HSTL_I, DIFF_HSTL_II	50	0	$V_{REF}$	0.75
DIFF_HSTL, Class I & II, 1.8V	DIFF_HSTL_I_18, DIFF_HSTL_II_18	50	0	$V_{REF}$	0.9
DIFF_HSUL_12, 1.2V	DIFF_HSUL_12	50	0	$V_{REF}$	0.6
DIFF_SSTL135/DIFF_SSTL135_R, 1.35V	DIFF_SSTL135, DIFF_SSTL135_R	50	0	$V_{REF}$	0.675
DIFF_SSTL15/DIFF_SSTL15_R, 1.5V	DIFF_SSTL15, DIFF_SSTL15_R	50	0	$V_{REF}$	0.75
DIFF_SSTL18, Class I & II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	50	0	$V_{REF}$	0.9
LVDS, 2.5V	LVDS_25	100	0	0 <sup>(2)</sup>	0
BLVDS (Bus LVDS), 2.5V	BLVDS_25	100	0	0 <sup>(2)</sup>	0
Mini LVDS, 2.5V	MINI_LVDS_25	100	0	0 <sup>(2)</sup>	0
PPDS_25	PPDS_25	100	0	0 <sup>(2)</sup>	0
RSDS_25	RSDS_25	100	0	0 <sup>(2)</sup>	0
TMDS_33	TMDS_33	50	0	0 <sup>(2)</sup>	3.3

**Notes:**

1.  $C_{REF}$  is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

## Input/Output Logic Switching Characteristics

Table 21: ILOGIC Switching Characteristics

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
<b>Setup/Hold</b>					
$T_{ICE1CK}/T_{ICKCE1}$	CE1 pin setup/hold with respect to CLK.	0.54/0.02	0.76/0.02	0.76/0.02	ns
$T_{ISRCK}/T_{ICKSR}$	SR pin setup/hold with respect to CLK.	0.70/0.01	1.13/0.01	1.13/0.01	ns
$T_{IDOCK}/T_{IOCKD}$	D pin setup/hold with respect to CLK without delay.	0.01/0.29	0.01/0.33	0.01/0.33	ns
$T_{IDOCKD}/T_{IOCKDD}$	DDLY pin setup/hold with respect to CLK (using IDELAY).	0.02/0.29	0.02/0.33	0.02/0.33	ns
<b>Combinatorial</b>					
$T_{IDI}$	D pin to O pin propagation delay, no delay.	0.11	0.13	0.13	ns
$T_{IDID}$	DDLY pin to O pin propagation delay (using IDELAY).	0.12	0.14	0.14	ns
<b>Sequential Delays</b>					
$T_{IDLO}$	D pin to Q1 pin using flip-flop as a latch without delay.	0.44	0.51	0.51	ns
$T_{IDLOD}$	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY).	0.44	0.51	0.51	ns
$T_{ICKQ}$	CLK to Q outputs.	0.57	0.66	0.66	ns
$T_{RQ\_ILOGIC}$	SR pin to OQ/TQ out.	1.08	1.32	1.32	ns
$T_{GSRQ\_ILOGIC}$	Global set/reset to Q outputs.	7.60	10.51	10.51	ns
<b>Set/Reset</b>					
$T_{RPW\_ILOGIC}$	Minimum pulse width, SR inputs.	0.72	0.72	0.72	ns, Min

## Input Serializer/Deserializer Switching Characteristics

Table 23: ISERDES Switching Characteristics

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
<b>Setup/Hold for Control Lines</b>					
T <sub>ISCKC_BITSLIP</sub> /T <sub>ISCKC_BITSLIP</sub>	BITSLIP pin setup/hold with respect to CLKDIV.	0.02/0.15	0.02/0.17	0.02/0.17	ns
T <sub>ISCKC_CE</sub> /T <sub>ISCKC_CE</sub>	CE pin setup/hold with respect to CLK (for CE1).	0.50/-0.01	0.72/-0.01	0.72/-0.01	ns
T <sub>ISCKC_CE2</sub> /T <sub>ISCKC_CE2</sub>	CE pin setup/hold with respect to CLKDIV (for CE2).	-0.10/0.36	-0.10/0.40	-0.10/0.40	ns
<b>Setup/Hold for Data Lines</b>					
T <sub>ISDCK_D</sub> /T <sub>ISCKD_D</sub>	D pin setup/hold with respect to CLK.	-0.02/0.14	-0.02/0.17	-0.02/0.17	ns
T <sub>ISDCK_DDLY</sub> /T <sub>ISCKD_DDLY</sub>	DDLY pin setup/hold with respect to CLK (using IDELAY). <sup>(1)</sup>	-0.02/0.14	-0.02/0.17	-0.02/0.17	ns
T <sub>ISDCK_D_DDR</sub> /T <sub>ISCKD_D_DDR</sub>	D pin setup/hold with respect to CLK at DDR mode.	-0.02/0.14	-0.02/0.17	-0.02/0.17	ns
T <sub>ISDCK_DDLY_DDR</sub> /T <sub>ISCKD_DDLY_DDR</sub>	D pin setup/hold with respect to CLK at DDR mode (using IDELAY). <sup>(1)</sup>	0.14/0.14	0.17/0.17	0.17/0.17	ns
<b>Sequential Delays</b>					
T <sub>ISCKO_Q</sub>	CLKDIV to out at Q pin.	0.54	0.66	0.66	ns
<b>Propagation Delays</b>					
T <sub>ISDO_DO</sub>	D input to DO output pin.	0.11	0.13	0.13	ns

**Notes:**

1. Recorded at 0 tap value.

## Output Serializer/Deserializer Switching Characteristics

Table 24: OSERDES Switching Characteristics

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
<b>Setup/Hold</b>					
T <sub>OSDCK_D</sub> /T <sub>OSCKD_D</sub>	D input setup/hold with respect to CLKDIV.	0.45/0.03	0.63/0.03	0.63/0.03	ns
T <sub>OSDCK_T</sub> /T <sub>OSCKD_T</sub>	T input setup/hold with respect to CLK.	0.73/-0.13	0.88/-0.13	0.88/-0.13	ns
T <sub>OSDCK_T2</sub> /T <sub>OSCKD_T2</sub>	T input setup/hold with respect to CLKDIV.	0.34/-0.13	0.39/-0.13	0.39/-0.13	ns
T <sub>OSCCK_OCE</sub> /T <sub>OSCKC_OCE</sub>	OCE input setup/hold with respect to CLK.	0.34/0.58	0.51/0.58	0.51/0.58	ns
T <sub>OSCCK_S</sub>	SR (reset) input setup with respect to CLKDIV.	0.52	0.85	0.85	ns
T <sub>OSCCK_TCE</sub> /T <sub>OSCKC_TCE</sub>	TCE input setup/hold with respect to CLK.	0.34/0.01	0.51/0.01	0.51/0.01	ns
<b>Sequential Delays</b>					
T <sub>oscko_oq</sub>	Clock to out from CLK to OQ.	0.42	0.48	0.48	ns
T <sub>oscko_tq</sub>	Clock to out from CLK to TQ.	0.49	0.56	0.56	ns
<b>Combinatorial</b>					
T <sub>osdo_ttq</sub>	T input to TQ out.	0.92	1.11	1.11	ns

## CLB Switching Characteristics

Table 27: CLB Switching Characteristics

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
<b>Combinatorial Delays</b>					
$T_{ILO}$	An – Dn LUT address to A.	0.11	0.13	0.13	ns, Max
$T_{ILO\_2}$	An – Dn LUT address to AMUX/CMUX.	0.30	0.36	0.36	ns, Max
$T_{ILO\_3}$	An – Dn LUT address to BMUX_A.	0.46	0.55	0.55	ns, Max
$T_{ITO}$	An – Dn inputs to A – D Q outputs.	1.05	1.27	1.27	ns, Max
$T_{AXA}$	AX inputs to AMUX output.	0.69	0.84	0.84	ns, Max
$T_{AXB}$	AX inputs to BMUX output.	0.66	0.83	0.83	ns, Max
$T_{AXC}$	AX inputs to CMUX output.	0.68	0.82	0.82	ns, Max
$T_{AXD}$	AX inputs to DMUX output.	0.75	0.90	0.90	ns, Max
$T_{BXB}$	BX inputs to BMUX output.	0.57	0.69	0.69	ns, Max
$T_{BxD}$	BX inputs to DMUX output.	0.69	0.82	0.82	ns, Max
$T_{CXC}$	CX inputs to CMUX output.	0.48	0.58	0.58	ns, Max
$T_{CXD}$	CX inputs to DMUX output.	0.59	0.71	0.71	ns, Max
$T_{DXD}$	DX inputs to DMUX output.	0.58	0.70	0.70	ns, Max
<b>Sequential Delays</b>					
$T_{CKO}$	Clock to AQ – DQ outputs.	0.44	0.53	0.53	ns, Max
$T_{SHCKO}$	Clock to AMUX – DMUX outputs.	0.53	0.66	0.66	ns, Max
<b>Setup and Hold Times of CLB Flip-Flops Before/After Clock CLK</b>					
$T_{AS}/T_{AH}$	AN – DN input to CLK on A – D flip-flops.	0.09/0.14	0.11/0.18	0.11/0.18	ns, Min
$T_{DICK}/T_{CKDI}$	AX – DX input to CLK on A – D flip-flops.	0.07/0.21	0.09/0.26	0.09/0.26	ns, Min
	AX – DX input through MUXs and/or carry logic to CLK on A – D flip-flops.	0.66/0.09	0.81/0.11	0.81/0.11	ns, Min
$T_{CECK\_CLB}/T_{CKCE\_CLB}$	CE input to CLK on A – D flip-flops.	0.17/0.00	0.21/0.01	0.21/0.01	ns, Min
$T_{SRCK}/T_{CKSR}$	SR input to CLK on A – D flip-flops.	0.43/0.04	0.53/0.05	0.53/0.05	ns, Min
<b>Set/Reset</b>					
$T_{SRMIN}$	SR input minimum pulse width.	0.78	1.04	1.04	ns, Min
$T_{RQ}$	Delay from SR input to AQ – DQ flip-flops.	0.59	0.71	0.71	ns, Max
$T_{CEO}$	Delay from CE input to AQ – DQ flip-flops.	0.58	0.70	0.70	ns, Max
$F_{TOG}$	Toggle frequency (for export control).	1286	1098	1098	MHz

## Block RAM and FIFO Switching Characteristics

Table 30: Block RAM and FIFO Switching Characteristics

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
<b>Block RAM and FIFO Clock-to-Out Delays</b>					
T <sub>RCKO_DO</sub> and T <sub>RCKO_DO_REG</sub>	Clock CLK to DOUT output (without output register). <sup>(1)(2)</sup>	2.13	2.46	2.46	ns, Max
	Clock CLK to DOUT output (with output register). <sup>(3)(4)</sup>	0.74	0.89	0.89	ns, Max
T <sub>RCKO_DO_ECC</sub> and T <sub>RCKO_DO_ECC_REG</sub>	Clock CLK to DOUT output with ECC (without output register). <sup>(1)(2)</sup>	3.04	3.84	3.84	ns, Max
	Clock CLK to DOUT output with ECC (with output register). <sup>(3)(4)</sup>	0.81	0.94	0.94	ns, Max
T <sub>RCKO_DO_CASCOUP</sub> and T <sub>RCKO_DO_CASCOUP_REG</sub>	Clock CLK to DOUT output with cascade (without output register). <sup>(1)</sup>	2.88	3.30	3.30	ns, Max
	Clock CLK to DOUT output with cascade (with output register). <sup>(3)</sup>	1.28	1.46	1.46	ns, Max
T <sub>RCKO_FLAGS</sub>	Clock CLK to FIFO flags outputs. <sup>(5)</sup>	0.87	1.05	1.05	ns, Max
T <sub>RCKO_POINTERS</sub>	Clock CLK to FIFO pointers outputs. <sup>(6)</sup>	1.02	1.15	1.15	ns, Max
T <sub>RCKO_PARITY_ECC</sub>	Clock CLK to ECCPARITY in ECC encode only mode.	0.85	0.94	0.94	ns, Max
T <sub>RCKO_SDBIT_ECC</sub> and T <sub>RCKO_SDBIT_ECC_REG</sub>	Clock CLK to BITERR (without output register).	2.81	3.55	3.55	ns, Max
	Clock CLK to BITERR (with output register).	0.76	0.89	0.89	ns, Max
T <sub>RCKO_RDADDR_ECC</sub> and T <sub>RCKO_RDADDR_ECC_REG</sub>	Clock CLK to RDADDR output with ECC (without output register).	0.88	1.07	1.07	ns, Max
	Clock CLK to RDADDR output with ECC (with output register).	0.93	1.08	1.08	ns, Max
<b>Setup and Hold Times Before/After Clock CLK</b>					
T <sub>RCKC_ADDRA</sub> / T <sub>RCKC_ADDRA</sub>	ADDR inputs. <sup>(7)</sup>	0.49/0.33	0.57/0.36	0.57/0.36	ns, Min
T <sub>RDCK_DI_WF_NC</sub> / T <sub>RCKD_DI_WF_NC</sub>	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode. <sup>(8)</sup>	0.65/0.63	0.74/0.67	0.74/0.67	ns, Min
T <sub>RDCK_DI_RF</sub> / T <sub>RCKD_DI_RF</sub>	Data input setup/hold time when block RAM is configured in READ_FIRST mode. <sup>(8)</sup>	0.22/0.34	0.25/0.41	0.25/0.41	ns, Min
T <sub>RDCK_DI_ECC</sub> / T <sub>RCKD_DI_ECC</sub>	DIN inputs with block RAM ECC in standard mode. <sup>(8)</sup>	0.55/0.46	0.63/0.50	0.63/0.50	ns, Min
T <sub>RDCK_DI_ECCW</sub> / T <sub>RCKD_DI_ECCW</sub>	DIN inputs with block RAM ECC encode only. <sup>(8)</sup>	1.02/0.46	1.17/0.50	1.17/0.50	ns, Min

## DSP48E1 Switching Characteristics

Table 31: DSP48E1 Switching Characteristics

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
<b>Setup and Hold Times of Data/Control Pins to the Input Register Clock</b>					
$T_{DSPDCK\_A\_AREG}/$ $T_{DSPCKD\_A\_AREG}$	A input to A register CLK.	0.30/ 0.13	0.37/ 0.14	0.37/ 0.14	ns
$T_{DSPDCK\_B\_BREG}/$ $T_{DSPCKD\_B\_BREG}$	B input to B register CLK.	0.38/ 0.16	0.45/ 0.18	0.45/ 0.18	ns
$T_{DSPDCK\_C\_CREG}/$ $T_{DSPCKD\_C\_CREG}$	C input to C register CLK.	0.20/ 0.19	0.24/ 0.21	0.24/ 0.21	ns
$T_{DSPDCK\_D\_DREG}/$ $T_{DSPCKD\_D\_DREG}$	D input to D register CLK.	0.32/ 0.27	0.42/ 0.27	0.42/ 0.27	ns
$T_{DSPDCK\_ACIN\_AREG}/$ $T_{DSPCKD\_ACIN\_AREG}$	ACIN input to A register CLK.	0.27/ 0.13	0.32/ 0.14	0.32/ 0.14	ns
$T_{DSPDCK\_BCIN\_BREG}/$ $T_{DSPCKD\_BCIN\_BREG}$	BCIN input to B register CLK.	0.29/ 0.16	0.36/ 0.18	0.36/ 0.18	ns
<b>Setup and Hold Times of Data Pins to the Pipeline Register Clock</b>					
$T_{DSPDCK\_{A, B}\_MREG\_MULT}/$ $T_{DSPCKD\_{A, B}\_MREG\_MULT}$	{A, B} input to M register CLK using multiplier.	2.76/ -0.01	3.29/ -0.01	3.29/ -0.01	ns
$T_{DSPDCK\_{A, D}\_ADREG}/$ $T_{DSPCKD\_{A, D}\_ADREG}$	{A, D} input to AD register CLK.	1.48/ -0.02	1.76/ -0.02	1.76/ -0.02	ns
<b>Setup and Hold Times of Data/Control Pins to the Output Register Clock</b>					
$T_{DSPDCK\_{A, B}\_PREG\_MULT}/$ $T_{DSPCKD\_{A, B}\_PREG\_MULT}$	{A, B} input to P register CLK using multiplier.	4.60/ -0.28	5.48/ -0.28	5.48/ -0.28	ns
$T_{DSPDCK\_D\_PREG\_MULT}/$ $T_{DSPCKD\_D\_PREG\_MULT}$	D input to P register CLK using multiplier.	4.50/ -0.73	5.35/ -0.73	5.35/ -0.73	ns
$T_{DSPDCK\_{A, B}\_PREG}/$ $T_{DSPCKD\_{A, B}\_PREG}$	A or B input to P register CLK not using multiplier.	1.98/ -0.28	2.35/ -0.28	2.35/ -0.28	ns
$T_{DSPDCK\_C\_PREG}/$ $T_{DSPCKD\_C\_PREG}$	C input to P register CLK not using multiplier.	1.76/ -0.26	2.10/ -0.26	2.10/ -0.26	ns
$T_{DSPDCK\_PCIN\_PREG}/$ $T_{DSPCKD\_PCIN\_PREG}$	PCIN input to P register CLK.	1.51/ -0.15	1.80/ -0.15	1.80/ -0.15	ns
<b>Setup and Hold Times of the CE Pins</b>					
$T_{DSPDCK\_{CEA; CEB}\_{AREG; BREG}}/$ $T_{DSPCKD\_{CEA; CEB}\_{AREG; BREG}}$	{CEA; CEB} input to {A; B} register CLK.	0.42/ 0.08	0.52/ 0.11	0.52/ 0.11	ns
$T_{DSPDCK\_CEC\_CREG}/$ $T_{DSPCKD\_CEC\_CREG}$	CEC input to C register CLK.	0.34/ 0.11	0.42/ 0.13	0.42/ 0.13	ns
$T_{DSPDCK\_CED\_DREG}/$ $T_{DSPCKD\_CED\_DREG}$	CED input to D register CLK.	0.43/ -0.03	0.52/ -0.03	0.52/ -0.03	ns

## Clock Buffers and Networks

Table 32: Global Clock Switching Characteristics (Including BUFGCTRL)

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{BCCCK\_CE}/T_{BCCKC\_CE}$ <sup>(1)</sup>	CE pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
$T_{BCCCK\_S}/T_{BCCKC\_S}$ <sup>(1)</sup>	S pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
$T_{BGCKO\_O}$ <sup>(2)</sup>	BUFGCTRL delay from I0/I1 to O.	0.09	0.10	0.10	ns
<b>Maximum Frequency</b>					
$F_{MAX\_BUFG}$	Global clock tree (BUFG).	628.00	464.00	464.00	MHz

**Notes:**

- $T_{BCCCK\_CE}$  and  $T_{BCCKC\_CE}$  must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
- $T_{BGCKO\_O}$  (BUFG delay from I0 to O) values are the same as  $T_{BCCKO\_O}$  values.

Table 33: Input/Output Clock Switching Characteristics (BUFIO)

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{BIOCKO\_O}$	Clock to out delay from I to O.	1.26	1.54	1.54	ns
<b>Maximum Frequency</b>					
$F_{MAX\_BUFIO}$	I/O clock tree (BUFIO).	680.00	600.00	600.00	MHz

Table 34: Regional Clock Buffer Switching Characteristics (BUFR)

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{BRCKO\_O}$	Clock to out delay from I to O.	0.76	0.99	0.99	ns
$T_{BRCKO\_O\_BYP}$	Clock to out delay from I to O with Divide Bypass attribute set.	0.39	0.52	0.52	ns
$T_{BRDO\_O}$	Propagation delay from CLR to O.	0.85	1.09	1.09	ns
<b>Maximum Frequency</b>					
$F_{MAX\_BUFR}$ <sup>(1)</sup>	Regional clock tree (BUFR).	375.00	315.00	315.00	MHz

**Notes:**

- The maximum input frequency to the BUFR is the BUFIO  $F_{MAX}$  frequency.

## MMCM Switching Characteristics

Table 37: MMCM Specification

Symbol	Description	V <sub>CCINT</sub> Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
MMCM_F <sub>INMAX</sub>	Maximum input clock frequency.	800.00	800.00	800.00	MHz
MMCM_F <sub>INMIN</sub>	Minimum input clock frequency.	10.00	10.00	10.00	MHz
MMCM_F <sub>INJITTER</sub>	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max			
MMCM_F <sub>INDUTY</sub>	Allowable input duty cycle: 10—49 MHz.	25	25	25	%
	Allowable input duty cycle: 50—199 MHz.	30	30	30	%
	Allowable input duty cycle: 200—399 MHz.	35	35	35	%
	Allowable input duty cycle: 400—499 MHz.	40	40	40	%
	Allowable input duty cycle: > 500 MHz.	45	45	45	%
MMCM_F <sub>MIN_PSCLK</sub>	Minimum dynamic phase-shift clock frequency.	0.01	0.01	0.01	MHz
MMCM_F <sub>MAX_PSCLK</sub>	Maximum dynamic phase-shift clock frequency.	500.00	450.00	450.00	MHz
MMCM_F <sub>VCOMIN</sub>	Minimum MMCM VCO frequency.	600.00	600.00	600.00	MHz
MMCM_F <sub>VCOMAX</sub>	Maximum MMCM VCO frequency.	1440.00	1200.00	1200.00	MHz
MMCM_F <sub>BANDWIDTH</sub>	Low MMCM bandwidth at typical. <sup>(1)</sup>	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical. <sup>(1)</sup>	4.00	4.00	4.00	MHz
MMCM_T <sub>STATPHAOFFSET</sub>	Static phase offset of the MMCM outputs. <sup>(2)</sup>	0.12	0.12	0.12	ns
MMCM_T <sub>OUTJITTER</sub>	MMCM output jitter.	Note 3			
MMCM_T <sub>OUTDUTY</sub>	MMCM output clock duty-cycle precision. <sup>(4)</sup>	0.20	0.20	0.20	ns
MMCM_T <sub>LOCKMAX</sub>	MMCM maximum lock time.	100.00	100.00	100.00	μs
MMCM_F <sub>OUTMAX</sub>	MMCM maximum output frequency.	800.00	800.00	800.00	MHz
MMCM_F <sub>OUTMIN</sub>	MMCM minimum output frequency. <sup>(5)(6)</sup>	4.69	4.69	4.69	MHz
MMCM_T <sub>EXTFDVAR</sub>	External clock feedback variation.	< 20% of clock input period or 1 ns Max			
MMCM_RST <sub>MINPULSE</sub>	Minimum reset pulse width.	5.00	5.00	5.00	ns
MMCM_F <sub>PFDMAX</sub>	Maximum frequency at the phase frequency detector.	500.00	450.00	450.00	MHz
MMCM_F <sub>PFDMIN</sub>	Minimum frequency at the phase frequency detector.	10.00	10.00	10.00	MHz
MMCM_T <sub>FBDELAY</sub>	Maximum delay in the feedback path.	3 ns Max or one CLKIN cycle			
<b>MMCM Switching Characteristics Setup and Hold</b>					
T <sub>MMCMDCK_PSEN</sub> / T <sub>MMCMCKD_PSEN</sub>	Setup and hold of phase-shift enable.	1.04/0.00	1.04/0.00	1.04/0.00	ns

Table 40: Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Far Clock Region)<sup>(1)</sup>

Symbol	Description	Device	$V_{CCINT}$ Operating Voltage and Speed Grade		Units	
			1.0V	0.95V		
			-2	-1		
<b>SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, without MMCM/PLL.</b>						
$T_{ICKOFFAR}$	Clock-capable clock input and OUTFF at pins/banks farthest from the BUFGs <i>without</i> MMCM/PLL (far clock region). <sup>(2)</sup>	XC7S6	5.55	6.50	6.50	ns
		XC7S15	5.55	6.50	6.50	ns
		XC7S25	5.55	6.44	6.44	ns
		XC7S50	5.71	6.62	6.62	ns
		XC7S75	6.01	7.02	7.02	ns
		XC7S100	6.01	7.02	7.02	ns
		XA7S6	5.55	6.50	N/A	ns
		XA7S15	5.55	6.50	N/A	ns
		XA7S25	5.55	6.44	N/A	ns
		XA7S50	5.71	6.62	N/A	ns
		XA7S75	6.01	7.02	N/A	ns
		XA7S100	6.01	7.02	N/A	ns

**Notes:**

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Refer to the *Die Level Bank Numbering Overview* section of the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 51: Configuration Switching Characteristics (Cont'd)

Symbol	Description	$V_{CCINT}$ Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B setup/hold.	4.00/0.00	4.00/0.00	4.00/0.00	ns, Min
$T_{SMWCCK}/T_{SMCCKW}$	RDWR_B setup/hold.	10.00/0.00	10.00/0.00	10.00/0.00	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 $\Omega$ pull-up resistor required).	7.00	7.00	7.00	ns, Max
$T_{SMCO}$	D[31:00] clock to out in readback.	8.00	8.00	8.00	ns, Max
$F_{RBCK}$	Readback frequency.	100.00	100.00	100.00	MHz, Max
<b>Boundary-Scan Port Timing Specifications</b>					
$T_{TAPTCK}/T_{TCKTAP}$	TMS and TDI setup/hold.	3.00/2.00	3.00/2.00	3.00/2.00	ns, Min
$T_{TCKTDO}$	TCK falling edge to TDO output.	7.00	7.00	7.00	ns, Max
$F_{TCK}$	TCK frequency.	66.00	66.00	66.00	MHz, Max
<b>SPI Flash Master Mode Programming Switching</b>					
$T_{SPIDCC}/T_{SPICCD}$	D[03:00] setup/hold.	3.00/0.00	3.00/0.00	3.00/0.00	ns, Min
$T_{SPICCM}$	MOSI clock to out.	8.00	8.00	8.00	ns, Max
$T_{SPICCF}$	FCS_B clock to out.	8.00	8.00	8.00	ns, Max
<b>STARTUPE2 Ports</b>					
$T_{USRCLKO}$	STARTUPE2 USRCLKO input to CCLK output.	0.50/6.70	0.50/7.50	0.50/7.50	ns, Min/Max
$F_{CFGMCLK}$	STARTUPE2 CFGMCLK output frequency.	65.00	65.00	65.00	MHz, Typ
$F_{CFGMCLKTOL}$	STARTUPE2 CFGMCLK output frequency tolerance.	$\pm 50$	$\pm 50$	$\pm 50$	%, Max
<b>Device DNA Access Port</b>					
$F_{DNACK}$	DNA access port (DNA_PORT).	100.00	100.00	100.00	MHz, Max

**Notes:**

- To support longer delays in configuration, use the design solutions described in the *7 Series FPGA Configuration User Guide* (UG470) [Ref 10].
- See the *7 Series FPGAs Overview* (DS180) [Ref 1] and *XA Spartan-7 Automotive FPGA Data Sheet: Overview* (DS171) [Ref 2] for a list of devices that support bitstream encryption.